Central
Semiconductor Corp.
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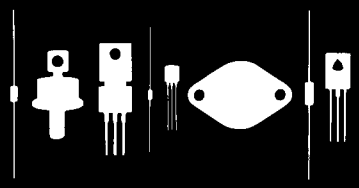
145 Adams Avenue
Hauppauge, New York 11788



2N4918
2N4919
2N4920

PNP Silicon Transistor
General Purpose Power

JEDEC TO-126 Case

DESCRIPTION

The CENTRAL SEMICONDUCTOR 2N4918, 2N4919, and 2N4920 are Silicon PNP Expitaxial Base Power Transistors designed for Medium power amplifer and switching applications.

MAXIMUM RATINGS (T_A=25°C Unless otherwise noted)

		2N4918	2N4919	2N4920
Collector-Base Voltage	V_{CBO}	40V	60V	80V
Collector-Emitter Voltage	V_{CEO}	40V	60V	80V
Emitter-Base Voltage	V_{EBO}		5.0V	
Collector Current, Continuous	I_C		1.0A	
Collector Current, Peak	I_{CM}		3.0A	
Base Current	I_B		1.0A	
Power Dissipation (T_C=25°C)	P_D		30W	
Operating & Storage Junction Temperature	T_J, T_{stg}		-65 to +150°C	
Thermal Resistance, Junction to Case	Θ_{J-C}		3.12°C/W	

ELECTRICAL CHARACTERISTICS (T_C=25°C)

SYMBOL	TEST CONDITIONS	MIN	MAX	UNIT
I_{CBO}	V_{CB}=Rated V_{CB}		100	uA
I_{CEV}	V_{CE}=Rated V_{CEO}, V_{EB}=1.5V		100	uA
I_{CEO}	V_{CE}=0.5X Rated V_{CEO}		500	uA
I_{EBO}	V_{EB}=5.0V		1.0	mA
BV_{CEO}	I_C=0.1A	40(2N4918)		V
		60(2N4919)		V
		80(2N4920)		V
$V_{CE(s)}$	I_C=1.0A, I_B=0.1A		0.6	V
$V_{BE(s)}$	I_C=1.0A, I_B=0.1A		1.3	V
$V_{BE(on)}$	V_{CE}=1.0V, I_C=1.0A		1.3	V
h_{FE}	V_{CE}=1.0V, I_C=50mA	40		-
h_{FE}	V_{CE}=1.0V, I_C=500mA	20	100	-
h_{FE}	V_{CE}=1.0V, I_C=1.0A	10		-
f_T	V_{CE}=10V, I_C=250mA, f=1.0MHz	3.0		MHz
C_{ob}	V_{CB}=10V, f=100KHz		100	pF

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